Dielectric constant of glasses: first observation of a two-dimensional behavior.

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The 1kHz real part χ' of the dielectric constant of a structural glass was measured at low temperature T down to 14 mK. Reducing the sample thickness h to 10 nm suppresses the usual minimum of χ' for measuring fields $E < .5$ MV/m. This contradicts the Two Level System (TLS) model but is well accounted for by including TLS-TLS interactions where excitations delocalize between TLS's through a E-induced mechanism recently designed: for small h's this interaction is reduced, which explains the two-dimensional behavior of $\chi'(T)$. Hence, interactions play a key role in standard thick samples.

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Since the 1970's amorphous solids have been widely investigated at low temperature T [1], and their properties turned out to be both "universal" (i.e. quasi independent from the chemical composition) and strongly different from their crystalline counterparts. This is explained within the tunneling two-level system (TLS) model [2] where some atomic species fluctuate between two neighboring energy minima separated by a potential barrier, which, at low T is crossed by Tunneling.

Even if the low density of glasses (in comparison with their crystalline counterpart) may justify [3] the existence of "voids" and thus the TLS framework, the ability of the standard TLS model, where the TLS's do *not* mutually interact, to account for experiments seems very intriguing. Indeed, drawing from measurements the coupling strength of a TLS to phonons, one finds [4] that TLS's are *strongly coupled to each other* via *virtual phonons*: a tunnel transition on a given TLS deforms elastically the neighboring matrix, yielding an energy change of $U \propto 1/r^3$ for a TLS located at a distance r, and for two neighboring TLS's [5] one gets $U(r = 1 \text{ nm}) \simeq 10$ K. Similarly, since many TLS's are charged, they interact through dipolar interaction, mediated by *virtual photons*, yielding an interaction energy [5] in the same range of 10 K between neighboring TLS's. This large energy scale contrasts with the weakness of the rare experimental evidences of TLS's interactions: in the 100 mK range, only small instationarities [6], and unexpected small H effects [7], on the kHz dielectric susceptibility χ have been related to interactions. In the few mK range, somewhat larger effects, such as the ultra-low-T plateau [8] in the dielectric constant, and the internal friction behavior [9], were explained with interactions.

This work yields *strong* evidence of the key role of TLS's interactions in the 100 mK range. Indeed, we show that reducing the thickness h of glassy samples down to 10 nm strongly affects the real part χ' of the 1 kHz dielectric constant: the $\chi'(T)$ minimum, which occurs at a given T_{rev} for $h > 100$ nm, is progressively *moved to lower* T as h *is decreased*, and finally disappears for $h \simeq 10$ nm. This new $\chi'(T)$ behavior contradicts the non interacting TLS model and evidences the role of TLS's interactions, since the latter are strongly reduced at small h's, as we shall see. Within the spectrum of theories dealing with interactions in the TLS model, ranging from the one stating that interactions are renormalized to zero by frustration [10], to the one assuming that interactions supersede disorder [11], the mechanism proposed by Burin *et al.* [12] will prove to account for the reported data, once included in numerical simulations of χ' [13].

The samples were all produced *similarly*: on a vitreous a-SiO_2 0.1 mm thick substrate, a Cu/glass/Cu/glass structure was deposited, by using a multi chamber system excluding exposure to air during the *whole* process [14]. The 15 nm thick Cu electrodes were evaporated (.1nm/s), while the glass layers were made from TetraEthylOrthoSilane with a 13 MHz vapor plasma where the autopolarisation was set at -100 V, the incoming flux at 2 sccm, and the pressure at 0.80 Pa. The resulting glass deposition rate was .1 nm/s, allowing to set the thickness h of the internal glass layer by choosing the deposition time. Since the h value is crucial, it was further measured by three other methods which all gave compatible results: *i)* in situ laser interferometry was realized onto a Si substrate placed close to the sample during the glass deposition; *ii)* the glass layer (the one grown onto the Si substrate) was irradiated by a deuton .91 MeV beam allowing, through the nuclear reaction on $_{16}$O, an h estimate; *iii)* the value of the capacitance $C \propto \chi'$ was checked to scale with the expected h. The 15 nm thick top glass layer hinders any spurious atmospheric effect during the cryogenic experiment. The sample was glued inside a copper box connected to the mixing chamber of the $_3$He/$_4$He dilution refrigerator. Semi-rigid coaxial shielding was ensured from the cold copper box up to the 2500-Andeen capacitance bridge. A capacitance c_F, twice larger than that of the sample, was set in parallel of each cable, so as to filter high frequency parasitic fields: the data were unchanged when c_F was halved, proving the filtering efficiency.

The $\chi'(T, E)$ behavior of six samples, whose h ranges from 12 nm to 800 nm, are reported in Figs. 1-3, where

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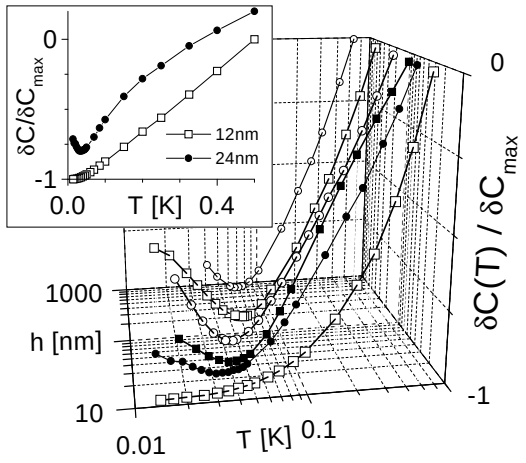

FIG. 1: For a given measuring field $E = 40$ kV/m, relative variation with T of the capacitance: as the sample thickness h decreases the minimum shifts towards lower T, disappearing for the lowest h. This contradicts the standard *non interacting* two-level system model. As the dissipated power $\mathcal{P} \propto E^2 h$ increases with h, this h effect cannot be due to heating by E. Inset: Same plot (T in linear scale), the 24 nm curve is vertically moved (+0.2) for clarity. For $h = 12$ nm, $\delta C(T) \propto T^\alpha$ instead of the standard $\ln T$ behavior obeyed for $h = 24$ nm.

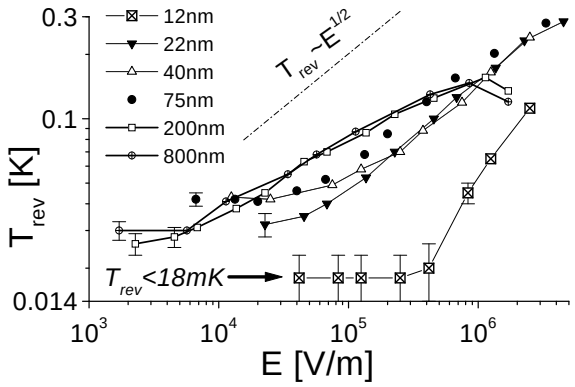

FIG. 2: Temperature T_{rev} of the minimum of $\chi'(T) \propto C(T)$, as a function of E, at various h (labelling the curves). For $h = 12$ nm, no minimum occurs for χ' down to 14 mK, for 40 kV/m$< E <$ 250 kV/m, which is indicated by "$T_{rev} < 18$ mK". For $E > 10$ kV/m, i.e. above the linear regime, T_{rev} increases with h at any given E, except for $E \gtrsim 1$ MV/m where heating occurs for the $h > 100$ nm samples. For clarity, the ± 4 mK uncertainty is shown only for a few lowest T_{rev} .

$\delta C(T) = C(T) - C(0.5\text{ K})$ and $\delta C_{max} = C(0.5\text{ K}) - C_{min}$ while C_{min} is the minimum value of C in our T experimental range [14 mK; 0.5 K]. Fig. 1 shows that, for a given measuring field $E = 40$ kV/m, the temperature T_{rev}, where $\chi'(T)$ is minimum, gradually moves towards lower values as h is decreased. For the thinnest sample, the minimum is suppressed at $E = 40$ kV/m, and instead of the usual $\delta C(T) \propto \pm \ln T$ valid for thicker samples (as well as for all previously studied glasses [15]), one gets $\delta C(T) \propto T^\alpha$ where α turns from $1.35 \pm .15$ above 70 mK to $2.75 \pm .4$ below. Fig. 2 shows first that this trend of lowering T_{rev} when decreasing h holds for all E (except for the very few cases $E \geq 1$ MV/m where some heating arises, see below); and secondly that this $T_{rev}(h)$ decrease only occurs for $h < 100$ nm since the 200 nm and 800 nm samples behave similarly. Last, Fig. 3 shows, for the smallest h, that a minimum of $\chi'(T)$ is recovered when $E \gtrsim 1$ MV/m, and that the value of the slope below T_{rev} is weakened beside that of thick samples.

These new trends for $\chi'(T, E, h)$ are intrinsic to the glassy state, as we shall see by showing that they come neither from a heating effect, nor from a variation of the glass composition with h:

i) the E-induced dissipated power $\mathcal{P}$ might heat the sample to a temperature above the measured T. Since the thermal conductances decrease as T decreases, heating, at a given E, increases at low T, i.e. it is expected to stretch the $\chi'(T)$ curve by an amount increasing as T is lowered. Thus, one might wonder whether the data of Figs 1-2 are due to heating or not. This explanation is ruled out since, with $R \propto h$ the parallel resistance of the sample, one has $\mathcal{P} = E^2 h^2 / R \propto E^2 h$, i.e. $\mathcal{P}$ *increases* with h at a given E. Thus, if the data of Figs. 1-2 were mainly due to heating, T_{rev} would decrease for thick samples, at odds with Fig. 1. In fact, heating effects are clearly visible only for the two thickest samples and for the strongest E: T_{rev} is slightly lower at $E = 2$ MV/m than at $E = 1$ MV/m. Assuming that, above the linear regime, i.e. when E is high enough to yield a $T_{rev}(E)$ increase, the law $T_{rev} \propto E^{1/2}$ is obeyed (see below), one can extract the thermal resistance $\mathcal{R}$ from the difference, increasing with E, between this law and the measured T_{rev}. From the two thickest samples one gets $\mathcal{R} \simeq 50$ MK/W at 100 mK, with a T^{-3} behavior, as expected for boundary Kapitza resistances.

ii) Besides, one may imagine that the data of Figs. 1-3 come from the fact that the glass composition depends on h, even for a given set of plasma parameters: due to a possible mixing of the plasma incoming particules and of the Cu of the first electrode, one may argue that the samples contain a "boundary" layer, of thickness b_0, whose chemical composition strongly differs of the rest of the glass (of thickness $h - b_0$). Since the value of T_{rev} slightly depends on the glass composition [15], one may wonder whether this could explain the reported data. This is not the case. First because the T dependence of $\delta C(T)$ is *totally new* for $h = 12$ nm: $\delta C(T) \propto T^\alpha$, *clearly differs* from the usual $\delta C(T) \propto \pm \ln T$ behavior holding both for our thicker samples and for all the previously studied samples [15] whatever their chemical composition. Secondly, this scenario leads to add the admittances of the two consecutive dielectrics, with the χ' of the boundary layer given by the 12 nm thick sample, and that of the second dielectric by the $h > 100$ nm samples. Applying this method for the 24 nm thick sample, at $E = 40$

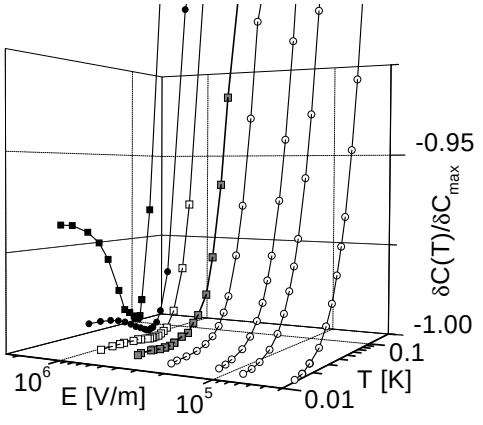

FIG. 3: For $h = 12$ nm, relative variation of the capacitance with T, at various E. No minimum occurs in $\chi'(T)$ down to 14 mK for the four lowest E's, contrarily to the three highest ones. At $E \simeq .4$ MV/m (in gray) one may have $T_{rev} = 19$ mK. The vertical scale is reduced beside that of Fig. 1, since the $\chi'(T < T_{rev})$ increase is weaker than in thick samples.

kV/m, one finds first that T_{rev} is halved in comparison with thick samples, as observed on Fig. 2; and secondly that $\delta C(T)$ should be dominated by far by the T^{α} behavior, which is *clearly contradicted* by Fig. 1 where the $\ln T$ trend holds for the 24 nm thick sample.

At this step, it is clear that *decreasing h qualitatively changes the physics of the glass sample*. This contradicts the standard (i.e. non interacting) TLS model which accounts for the decrease of χ' above T_{rev} by the progressive freezing of the diagonal (or relaxationnal) part χ'_z of the susceptibility, while the χ' increase below T_{rev} comes from the off-diagonal (or resonnant) part χ'_x: due to its pure quantum nature, χ'_x grows when T decreases, as do all quantum effects. Within this framework, the TLS's interactions are assumed to be so small that they only enter in the phase coherence time τ_2 setting the scale over which χ'_x relaxes towards its thermodynamic value. Since decreasing h reduces TLS's interactions (see below), one expects qualitatively larger τ_2 in thin samples, reinforcing somehow χ'_x, which is *at odds with* Figs.1-2. Quantitatively, in usual thick samples $\tau_2 \simeq 10$ μs in the 20 mK range, i.e. its value is so large that the associated quantum energy $\propto \tau_2^{-1}$ is as low as 1 μK, much smaller than any relevant energy scale, which explains that χ'_x does basically not depend on τ_2. Thus, *no h effect can be explained within the standard TLS model*.

Besides, another serious limit of the standard TLS model, discovered very recently [13], is that it does not account for the nonlinear $\chi'(T, E)$ usually reported (such as those of our $h > 100$ nm samples and those of Ref. [15]). Indeed, due to the quantum nature of χ' below T_{rev}, χ' is strongly *depressed* by a strong measuring electric field E at a given T. This is due to the *quantum saturation* phenomenon coming from the fact that increasing E decreases the population difference between the two energy levels: as the Rabi oscillations produced by E on the upper level are in phase opposition with respect to those produced on the ground level, the quantum response, once averaged on many independent TLS's, tends to zero when E is increased. This was checked by solving numerically the Bloch equations of TLS's [13] with a non perturbative method (see the dotted lines in Fig. 4).

Both the nonlinear measurements as well as the h effect on χ' can be accounted for by using the *same* E-induced TLS-TLS interaction proposed by Burin *et al.* [12] where thermal excitations, which are at zero-field localized on each TLS, tend to delocalize by hopping to resonant nearest neighbors. This is due to the fact that *resonant hopping* demands that *both* TLS's should have approximately the same asymmetry energy Δ *and* the same tunneling energy Δ_0: as the electrical field modulates the TLS parameter Δ, the probability of finding, for a given TLS, a resonant TLS, increases from a negligible value at very low E, to a non-negligible value above at higher E. Since this mechanism transports energy, it mainly enhances the diagonal part χ'_z of the susceptibility (by decreasing the associated relaxation time τ_1), and since it gets stronger as T decreases it yields the trend shown in Fig. 4 by the solid curves: in this picture, χ' mainly comes from χ'_z which dominates, *at any* T, over the off diagonal part χ'_x (the latter being still depressed by the E values used in experiments). With $\tau_1 \propto T/\sqrt{E}$, see Ref. [13], [5], Burin's mechanism is essential at low T, and is responsible for the $\chi'(T)$ increase below T_{rev} when $\omega\tau_1$ becomes smaller than unity, with ω the frequency of E. This yields $T_{rev} \propto \sqrt{E}$, *as seen on Fig. 2.*

In this picture, h effects on χ' are due to the two mechanisms reducing TLS's interactions at small h's. First, due to the usual density of states [1], if w is the maximum energy separating the gaps of two interacting TLS's, they are separated by the distance $\lambda \propto w^{-1/3}$ *only while* $\lambda < h$. For thin samples $h < \lambda$, the decrease of available TLS's yields $\lambda \propto w^{-1/2}$ and *enlarges* λ, reducing TLS's interactions $U \propto \lambda^{-3}$. This applies both to the elastic part of U where [5] one has $w \simeq T$, and to the dipolar part of U where Burin's mechanism states $w = e_{dip} = pE/\epsilon_r$ with $p \simeq 1$ D the TLS dipole and $\epsilon_r \simeq 5$ the glass dielectric constant [6], [15]. Secondly, dipolar interactions are further [17] reduced by the screening effect in the electrodes: if $h < \lambda$ their numerous electrons intercept and cancel the electric field yielding the interaction between TLS's, which sharply decreases U.

Finally, for $E = 40kV/m$ one gets $e_{dip} = 10$ mK, not far from the T range where the $\chi'(h)$ effects occur in Figs 1-2. Whatever $w = T$ or $w = e_{dip}$, the order of magnitude of $\lambda(w)$ is near 60 nm for thick samples: *this is consistent with the thickness where the* $\chi'(h)$ *effects occur in Figs. 1-2.* Since TLS's interactions bring about the $\chi'(T < T_{rev})$ behavior, their suppression at small h's should yield a $\chi'(T)$ curve given by the standard *non interacting* TLS model: as shown by the dotted lines in Fig. 4, this amounts to suppressing the $\chi'(T)$ minimum, *as in Fig. 1* for $h = 12$ nm, due to the E-induced strong de-

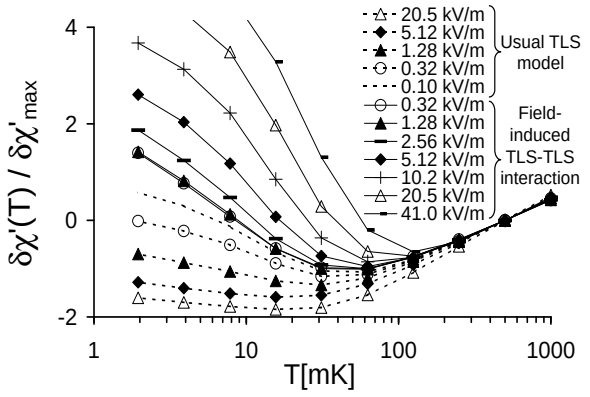

FIG. 4: Solving Bloch equations, $\chi'(T,E)$ was simulated in Ref. [13]. The non interacting TLS model yields the dotted lines: due to the quantum saturation effect, $\chi' \propto C$ is strongly depressed when rising E at low T, suppressing the minimum of $\chi'(T)$ for experimental fields $E > 40$ kV/m and modelling the 12 nm sample where TLS's interactions are strongly reduced. Including TLS's interactions through the E-induced mechanism of Ref. [12] restores the χ' increase with E at any given T, as well as that of T_{rev}: this models the usual $\chi'(T,E)$ of thick samples. Since strong E's decrease the distance λ between interacting TLS's, one recovers the usual behavior of $\chi'(T)$ when $\lambda(E) < h$: this explains, for $h = 12$ nm, the recovery of a $\chi'(T)$ minimum for strong E, as in Figs 2-3.

pression of χ'_x for the $E > 40$ kV/m experimental fields.

Besides, due to the E-induced modulation of Δ, in Burin *et al.*'s scenario λ decreases at strong E, opening the possibility to recover a $\lambda < h$ case at strong E: *this would account for Fig. 3* where, even for $h = 12$ nm, one recovers a minimum for $\chi'(T)$.

In conclusion, decreasing the thickness of glass samples down to the 10 nm range changes the physics of the real part of the kHz dielectric susceptibility. This strongly evidences the key role of TLS's interactions up to 100 mK. Assuming that TLS's interactions occur via a E-induced delocalisation of excitations between quasi similar TLS's accounts for the main features of the reported data.

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